

74V2T32

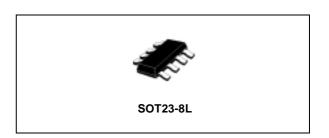
DUAL 2-INPUT OR GATE

- HIGH SPEED: $t_{PD} = 4.6$ ns (TYP.) at $V_{CC} = 5$ V
- LOW POWER DISSIPATION: $I_{CC} = 1\mu A(MAX.)$ at $T_A = 25$ °C
- COMPATIBLE WITH TTL OUTPUTS: V_{IH} = 2V (MIN), V_{IL} = 0.8V (MAX)
- POWER DOWN PROTECTION ON INPUTS SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 8mA (MIN)
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- OPERATING VOLTAGE RANGE: V_{CC}(OPR) = 4.5V to 5.5V
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The 74V2T32 is an advanced high-speed CMOS DUAL 2-INPUT OR GATE fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.



ORDER CODES

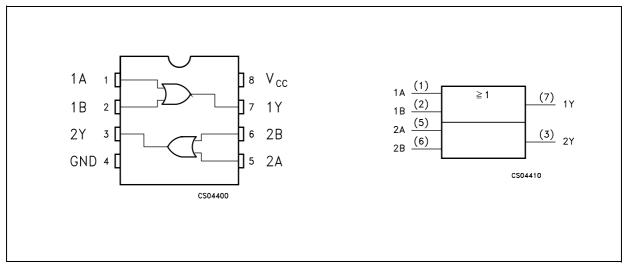
PACKAGE	T&R
SOT23-8L	74V2T32STR

Power down protection is provided on all inputs and outputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage.

This device can be used to interface 5V to 3V systems and it is ideal for portable applications like personal digital assistant and all battery-powered equipment.

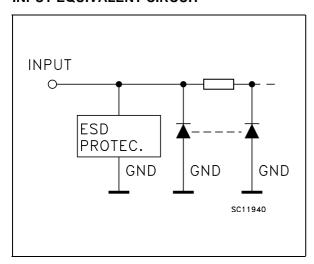
All inputs and outputs are equipped with protection circuits against static discharge, giving them ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



March 2004 1/7

INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN N°	SYMBOL	NAME QND FUNCTION		
1, 5	1A, 2A	Data Input		
2, 6	1B, 2B	Data Input		
7, 3	1Y, 2Y	Data Output		
4	GND	Ground (0V)		
8	V _{CC}	Positive Supply Voltage		

TRUTH TABLE

nA	nB	nY
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	4.5 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) ($V_{CC} = 5.0 \pm 0.5V$)	0 to 20	ns/V

1) V_{IN} from 0.8V to 2V

2/7

DC SPECIFICATIONS

		Т	est Condition				Value				
Symbol	Parameter	v _{cc}		Т	T _A = 25°C		-40 to 85°C		-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	4.5 to 5.5		2			2		2		V
V _{IL}	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V _{OH}	High Level Output	4.5	I _O =-50 μA	4.4	4.5		4.4		4.4		V
	Voltage	4.5	I _O =-8 mA	3.94			3.8		3.7		
V _{OL}	Low Level Output	4.5	I _O =50 μA		0.0	0.1		0.1		0.1	V
	Voltage	4.5	I _O =8 mA			0.36		0.44		0.55	
I ₁	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1.0		± 1.0	μА
I _{CC}	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	μА
+I _{CC}	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V _{CC} or GND			1.35		1.5		1.5	mA
I _{OPD}	Output Leakage Current	0	V _{OUT} = 5.5V			0.5		5.0		5.0	μА

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

		Test Condition		Value								
Symbol	Parameter	v _{cc}	CL		Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)	(pF)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{PLH}	Propagation Delay	5.0 (*)	15			4.6	7.0	1.0	8.0	1.0	9.0	20
t _{PHL}	Time	5.0 (*)	50			5.1	7.5	1.0	8.5	1.0	9.5	ns

^(*) Voltage range is $5.0V \pm 0.5V$

CAPACITANCE CHARACTERISTICS

		Test Condition		Value						
Symbol	Parameter		T _A = 25°C -40 to 85°C -55 to 12		125°C	Unit				
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance			4	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)			12						pF

¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/2$

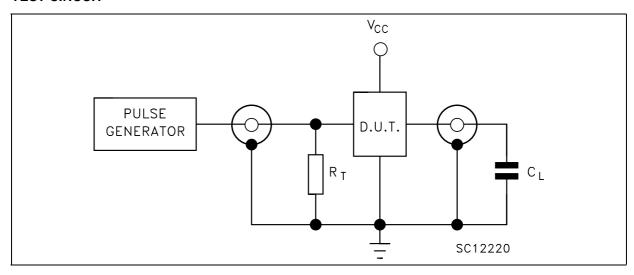
47/

DYNAMIC SWITCHING CHARACTERISTICS

		Tes	st Condition	Va		
Symbol	Parameter	V _{CC} (V)		T _A = 2	25 °C	Unit
		VCC (V)		Min.	Max.	
V _{OLP}	Dynamic Low Level Quiet Out-	5.0	C _L = 50pF		0.8	V
V _{OLV}	put (note 1)	5.0	$V_{IL} = 0V, V_{IH} = 3.3V$	-0.8		v

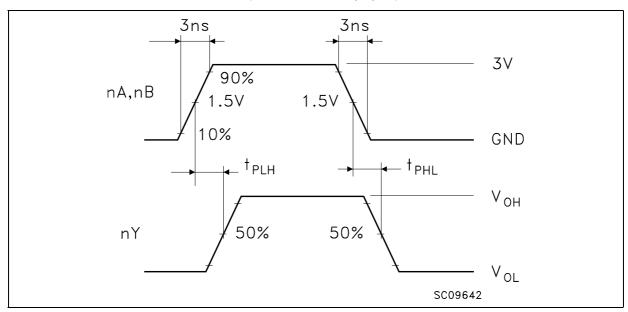
¹⁾ Number of output defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining outputs is measured in the LOW state.

TEST CIRCUIT



 C_L = 15/50pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically $50\Omega)$

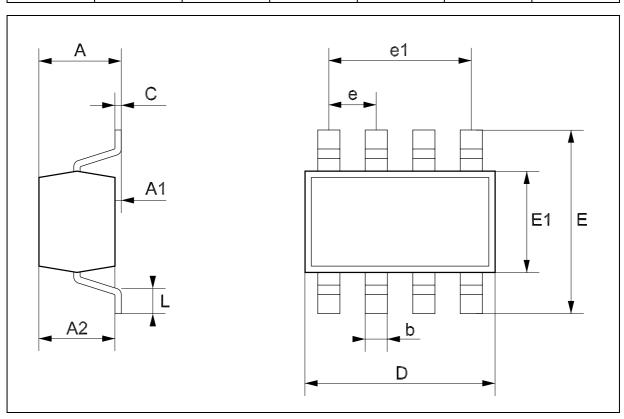
WAVEFORM: PROPAGATION DELAY (f=1MHz; 50% duty cycle)



47/ 4/7

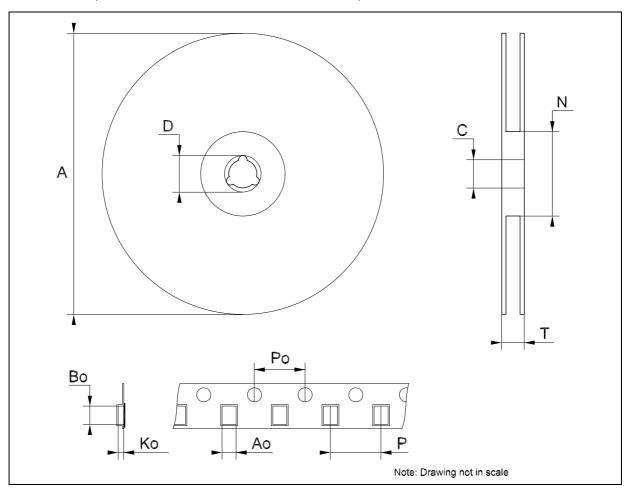
SOT23-8L MECHANICAL DATA

DIM		mm.			mils		
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	0.90		1.45	35.4		57.1	
A1	0.00		0.15	0.0		5.9	
A2	0.90		1.30	35.4		51.2	
b	0.22		0.38	8.6		14.9	
С	0.09		0.20	3.5		7.8	
D	2.80		3.00	110.2		118.1	
E	2.60		3.00	102.3		118.1	
E1	1.50		1.75	59.0		68.8	
е	0	.65			25.6		
e1		1.95			76.7		
L	0.35		0.55	13.7		21.6	



Tape &	Reel SOT23-xL	MECHANICAL	DATA
--------	---------------	-------------------	------

DIM.		mm.			inch	
DINI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			180			7.086
С	12.8	13.0	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	60			2.362		
Т			14.4			0.567
Ao	3.13	3.23	3.33	0.123	0.127	0.131
Во	3.07	3.17	3.27	0.120	0.124	0.128
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58
Ро	3.9	4.0	4.1	0.153	0.157	0.161
Р	3.9	4.0	4.1	0.153	0.157	0.161



6/7

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics All other names are the property of their respective owners

© 2004 STMicroelectronics - All Rights Reserved STMicroelectronics GROUP OF COMPANIES

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com



Copyright © Each Manufacturing Company.

All Datasheets cannot be modified without permission.

This datasheet has been download from:

www.AllDataSheet.com

100% Free DataSheet Search Site.

Free Download.

No Register.

Fast Search System.

www.AllDataSheet.com